

Amendments to the Claims

1. (Currently Amended) A method for forming a display device, comprising:

forming a thin film transistor (TFT), a gate pad and a data pad on a substrate;

depositing sequentially an inorganic insulating material and an organic insulating material on the substrate having the TFT, the gate pad and the data pad;

selectively removing the organic insulating material using a diffracting mask to form a patterned organic insulating layer;

selectively removing the inorganic insulating material, using at least a portion of the patterned organic insulating layer as a mask to define contact holes for the TFT, the gate pad and the data pad; and

selectively removing the patterned organic insulating layer as the organic insulating material is removed in the step of selectively removing the inorganic insulating material; and

forming electrodes in the contact holes.

2. (Canceled)

3. (Original) The method of claim 1, further comprising:

removing the patterned organic insulating layer corresponding to the gate and data pads after the step of selectively removing the inorganic insulating material is performed.

4. (Previously Presented) The method of claim 1, further comprising:

providing a gate insulating layer under the inorganic insulating material; and

selectively removing portions of the gate insulating layer corresponding to the gate pad, using said at least a portion of the patterned organic insulating layer as a mask.

5. (Original) The method of claim 1, wherein, in the step of forming the electrodes, the electrodes include an electrode in contact with the gate pad and the remaining inorganic insulating material, and an electrode in contact with the data pad and the remaining inorganic insulating material.

6. (New) The method of claim 1, wherein an ashing technique is employed in removing the organic insulating material.

7. (New) The method of claim 1, wherein a dry etching technique is employed in removing the organic insulating material.